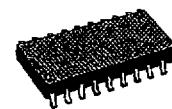


## MONOLITHIC TRANSIL® ARRAY FOR DATA LINE PROTECTION

### FEATURES

- HIGH SURGE CAPABILITY TRANSIL ARRAY  
 $I_{PP} = 40A \text{ } 8/20\mu s$
- UP TO 18 UNIDIRECTIONAL TRANSIL FUNCTIONS
- BREAKDOWN VOLTAGE = 6V1
- LOW CLAMPING FACTOR ( $V_{CL}/V_{BR}$ ) AT HIGH CURRENT LEVEL.



**SO 20**  
(Plastic)

### DESCRIPTION

This is a specific Transil Array for Centronics interface protection developed in monolithic chip form in order to provide a high surge capability and a low clamping voltage.

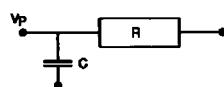
### IN ACCORDANCE WITH :

#### - ESD standard :

- . IEC 801-2      15kV      ns / 50ns
- . IEC 801-4      40A      5ns / 50ns
- . IEC 801-5      1KV      1.2 / 50 $\mu s$
- 25A      8/20 $\mu s$

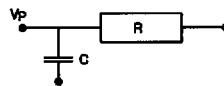
#### . MIL STD 883C - Methode 3015-2

$V_p = 25kV$   
 $C = 150pF$   
 $R = 150\Omega$   
 5 s duration

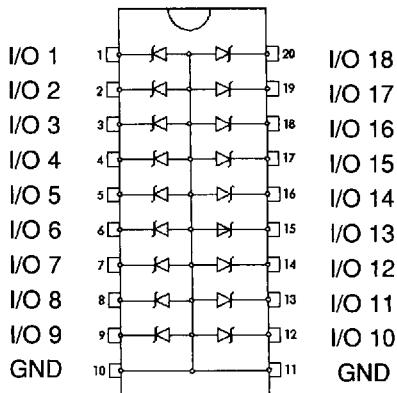


#### - Human body test :

$V_p = 4kV$   
 $C = 150pF$   
 $R = 150\Omega$



### FUNCTIONAL DIAGRAM

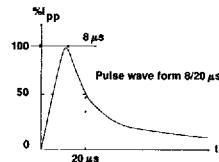


EQUIVALENT TO 18 UNIDIRECTIONAL TRANSILS

ABSOLUTE RATINGS (limiting values) ( $0^\circ\text{C} \leq \text{Tamb} \leq 70^\circ\text{C}$ )

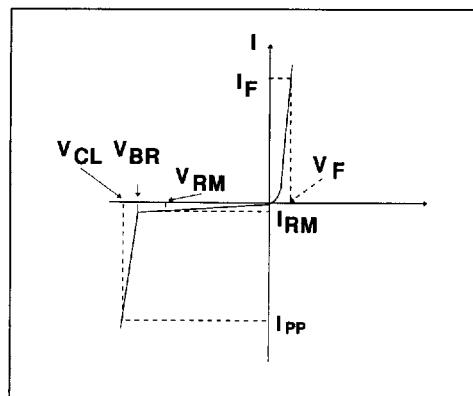
Symbol	Parameter		Value	Unit
I <sub>PP</sub>	Peak pulse current-8/20 $\mu\text{s}$	See note	40	A
I <sub>FSM</sub>	Non repetitive surge peak forward current	t <sub>p</sub> = 10 ms	6	
I <sub>2t</sub>	Wire I <sub>2t</sub> value	See note	0.6	A <sup>2</sup> s
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range		- 55 to + 150 125	°C °C

**Note :** For surges greater than the maximum value specified, the device will present first a short circuit to the common bus line and after an open circuit caused by the wire.  
These values are for each integrated diode.



## ELECTRICAL CHARACTERISTICS

Symbol	Parameter
V <sub>RM</sub>	Stand-off Voltage
V <sub>BR</sub>	Breakdown Voltage
V <sub>CCL</sub>	Clamping Voltage
I <sub>RM</sub>	Leakage Current @ V <sub>RM</sub>
I <sub>PP</sub>	Surge Current
C	Input Capacitance
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage Drop



Types	I <sub>RM</sub> @ V <sub>RM</sub>		V <sub>BR</sub> @ I <sub>R</sub>		V <sub>CCL</sub> @ I <sub>pp</sub>		V <sub>CCL</sub> @ I <sub>pp</sub>		V <sub>F</sub> @ I <sub>F</sub>	
	max	min note 1	V	mA	V	A	V	A	V	A
ITA6V1M3	50	5	6.1	1	12	10	14	25	1.5	1

Types	C 1		C 2		α <sub>T</sub> max
	max note 2	max note 3	pF	pF	
ITA6V1M3	1100		700		10 <sup>-4</sup> /°C 4

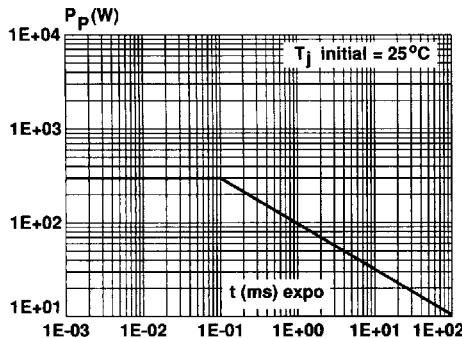
All parameters tested at 25°C, except where indicated

Note 1 : Between I<sub>0</sub> pin and ground

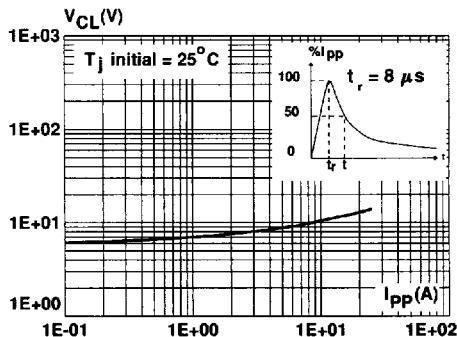
Note 2 : Between one input Pin at 0 V Bias and ground pin

Note 3 : Between one input pin at V<sub>RM</sub>, and ground pin.

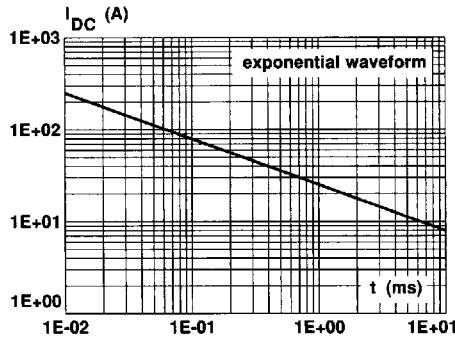
**Figure 1 : Peak pulse power versus exponential pulse duration.**



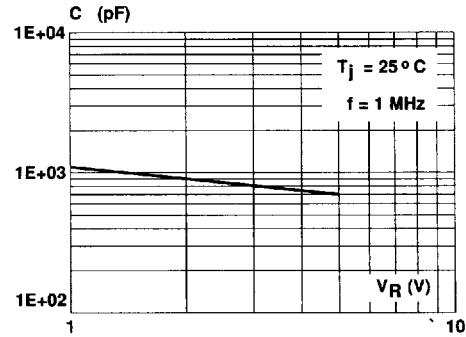
**Figure 2 : Clamping voltage versus peak pulse current exponential waveform 8/20 $\mu$ s**



**Figure 3 : Peak current I<sub>DC</sub> inducing open circuit of the wire for one input/output versus pulse duration (typical values).**

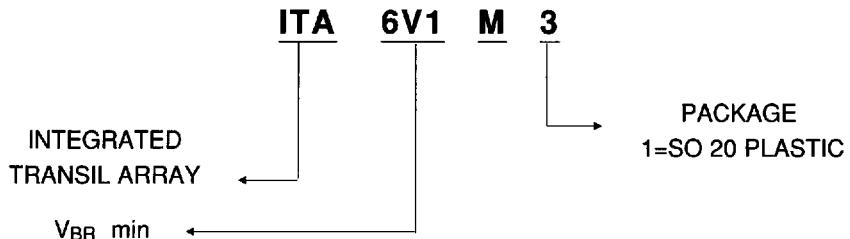


**Figure 4 : Junction capacitance versus reverse applied voltage for one input/output (typical values).**



Note : The curve of the figure 2 is specified for a junction temperature of  $25^\circ C$  before the surge

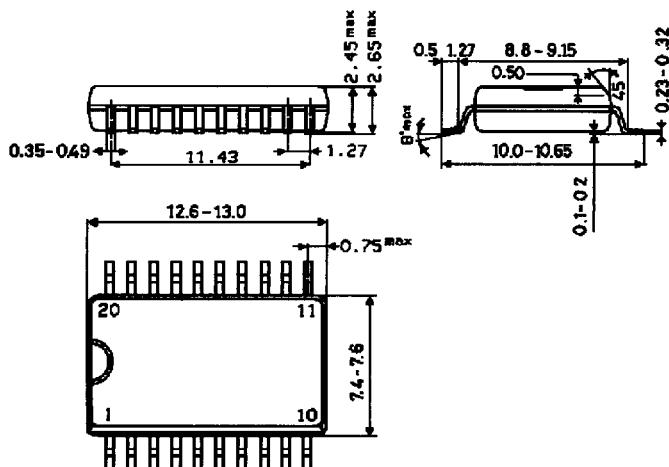
**ORDER CODE**



## **MARKING**

<b>TYPE</b>	<b>MARKING</b>
ITA6V1M3	ITA6V1M3

**PACKAGE MECHANICAL DATA** (in millimeters)  
SO 20 Plastic



**Packaging :** Products supplied in antistatic tubes.